

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L18	1	(memory or eeprom or eprom or prom) near15 (abrupt near3 diode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 10:35
L17	0	(memory or eeprom or eprom or prom) near15 (abrupt near diode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 10:35
L16	3	(memory or eeprom or eprom or prom) near15 (one adj side near diode or one adj sided near diode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 10:33
L8	433	(memory or eeprom or eprom or prom) and (antifus\$3 or anti-fus\$3) near10 (diode or "p+n" or "pn+" or "p-n+")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 10:31
L14	307	365/225.7.cor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 10:23
L13	97	438/600.cor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 10:23
L12	40	438/467.cor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 10:17
L11	157	(memory or eeprom or eprom or prom) and ((bit or digit) near line or bitline) and (wordline or word near line) and (diode) near8 ((heavily or highly or high) near2 (doped or doping))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 10:06
L10	80	(memory or eeprom or eprom or prom) and (diode) near8 ((heavily or highly or high) near2 (doped or doping)) near8 ((lightly or light or low) near2 (doped or doping))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 09:44
L9	15	(memory or eeprom or eprom or prom) and (antifus\$3 or anti-fus\$3) same (diode) near3 (heavily adj doped)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/10 09:35
L2	13	(memory or eeprom or eprom or prom) and (bitline or (bit or digit) near line) same (wordline or word near line) same ("p+n" or "pn+" or "p-n+" or one-side near diode or one-sided near diode)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/10 09:31

L3	10	(one-side near diode or one-sided near diode)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/10 09:30
L1	88	438/131.cor.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/10 09:28
S12	27	(memory or eeprom or eprom or prom) and (antifus\$3 or anti-fus\$3) and (multilayer or multi-layer or (plural or stacked or plurality) near (layer)) near4 (bit or digit or word)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 16:26
S18	281	257/530.cor.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 15:51
S17	83	257/209.cor.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 15:25
S16	126	257/208.cor.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 15:18
S15	113	257/204.cor.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 15:03
S14	256	257/202.cor.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 14:53
S13	32	257/50.cor.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 14:29
S11	92	(memory or eeprom or eprom or prom) and (antifus\$3 or anti-fus\$3) same ((rail or bar) near4 (conductor or stack or bit or digit) or (multilayer or multi-layer or barrier or silicide) near4 (bit or digit or word))	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 14:25
S9	24	("3913224" "4272880" "4442507" "4489478" "4498226" "4499557" "4500905" "4543594" "4646266" "4876220" "4881114" "5070384" "5306935" "5427979" "5535156" "5726484" "5745407" "5831325" "5835396" "5838530" "5991225" "6034882" "6160276" "6291836").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 14:20
S6	370	(three near dimensional or "3-dimensional" or "3-d" or vertically near stacked or vertical near matrix or stacked near matrix or stacked near cell) near4 (memory or prom or eeprom or eprom or worm or otp or storage) and (antifus\$4 or anti-fus\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 13:59
S4	10030	(three near dimensional or "3-dimensional" or "3-d" or vertically near stacked or vertical near matrix or stacked near matrix or stacked near cell) near4 (memory or prom or eeprom or eprom or worm or otp or storage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 13:55
S3	4	"6291836".pn. "4597162".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 13:53